TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MAR2245FK

Low-Voltage Octal Bus Transceiver with 3.6 V Tolerant Inputs and Outputs

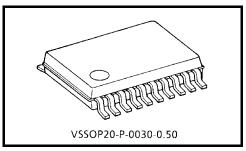
The TC7MAR2245FK is a high performance CMOS octal bus transceiver. Designed for use in 1.8, 2.5 or 3.3 V systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to $3.6\ V$.

The direction of data transmission is determined by the level of the DIR inputs. The \overline{OE} inputs can be used to disable the device so that the busses are effectively isolated.

The $26 \cdot \Omega$ series resistor helps reducing output overshoot and undershoot without external resistor.

All inputs are equipped with protection circuits against static discharge.



Weight: 0.03 g (typ.)

Features

- $26-\Omega$ series resistors on outputs.
- Low voltage operation: $V_{CC} = 1.8 \sim 3.6 \text{ V}$
- High speed operation:

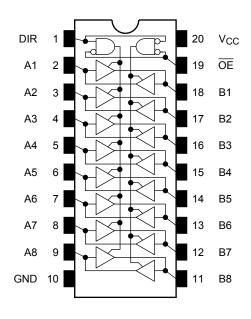
$$\begin{split} t_{pd} &= 4.4 \text{ ns (max) (V}_{CC} = 3.0 {\sim} 3.6 \text{ V)} \\ t_{pd} &= 5.6 \text{ ns (max) (V}_{CC} = 2.3 {\sim} 2.7 \text{ V)} \\ t_{pd} &= 9.8 \text{ ns (max) (V}_{CC} = 1.8 \text{ V)} \end{split}$$

- 3.6 V tolerant inputs and outputs.
- Output current: $I_{OH}/I_{OL} = \pm 12 \text{ mA (min)} (V_{CC} = 3.0 \text{ V})$

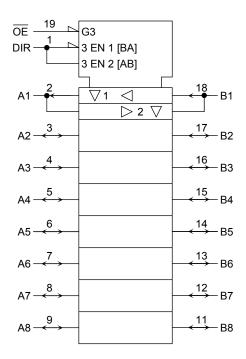
 $I_{OH}/I_{OL} = \pm 8$ mA (min) (V_{CC} = 2.3 V) $I_{OH}/I_{OL} = \pm 4$ mA (min) (V_{CC} = 1.8 V)

- Latch-up performance: -300 mA
- ESD performance: Machine model $\geq \pm 200~V$ Human body model $\geq \pm 2000~V$
- Package: VSSOP (US)
- Bidirectional interface between 2.5 V and 3.3 V signals. (*1)
- Power down protection is provided on all inputs and outputs. (*2)
- Supports live insertion/withdrawal (*3)
- Bidirectional interface between 2.5 V and 3.3 V signals. (*1)
- Power down protection is provided on all inputs and outputs. (*2)
- Supports live insertion/withdrawal (*3)
 - *1: Do not apply a signal to any bus terminal when it is in the output mode. Damage may result.
 - *2: All floating (high impedance) bus terminal must have their input level fixed by means of pull up or pull down resistors.
 - *3: To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

Pin Assignment (top view)



IEC Logic Symbol



Truth Table

Inp	uts	Outputs	Fun	ction
ŌĒ	DIR	Outputs	A-Bus	B-Bus
L	L	A = B	Output	Input
L	Н	B=A	Input	Output
Н	Х	Z	Z	

X: Don't care

Z: High impedance

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Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	-0.5~4.6	V
DC input voltage (DIR, OE)	V _{IN}	-0.5~4.6	V
DC bus I/O voltage	V _{I/O}	-0.5~4.6 (Note 2)	V
DC bus I/O voltage	V1/O	-0.5~V _{CC} + 0.5 (Note 3)	
Input diode current	l _{IK}	-50	mA
Output diode current	I _{OK}	±50 (Note 4)	mA
DC output current	lout	±50	mA
Power dissipation	P_{D}	180	mW
DC V _{CC} /ground current	I _{CC} /I _{GND}	±100	mA
Storage temperature	T _{stg}	-65~150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: Off-state

Note 3: High or low state. IOUT absolute maximum rating must be observed.

Note 4: Vout < GND, Vout > Vcc

Operating Ranges (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	1.8~3.6	V
Supply voltage	VCC	1.2~3.6 (Note 2)	V
Input voltage (DIR, $\overline{\sf OE}$)	V _{IN}	-0.3~3.6	V
Bus I/O voltage	Vuo	0~3.6 (Note 3)	V
Bus I/O voltage	V _{I/O}	0~V _{CC} (Note 4)	V
		±12 (Note 5)	
Output current	I _{OH} /I _{OL}	±8 (Note 6)	mA
		±4 (Note 7)	
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	0~10 (Note 8)	ns/V

Note 1: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs and bus inputs must be tied to either VCC or GND. Please connect both bus inputs and the bus outputs with VCC or GND when the I/O of the bus terminal changes by the function. In this case, please note that the output is not short-circuited.

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Note 2: Data retention only

Note 3: Off-state

Note 4: High or low state

Note 5: $V_{CC} = 3.0 \sim 3.6 \text{ V}$

Note 6: $V_{CC} = 2.3 \sim 2.7 \text{ V}$

Note 7: $V_{CC} = 1.8 \text{ V}$

Note 8: $V_{IN} = 0.8 \sim 2.0 \text{ V}, V_{CC} = 3.0 \text{ V}$



Electrical Characteristics

DC Characteristics (Ta = -40~85°C, 2.7 V < V_{CC} \leq 3.6 V)

Characteri	stics	Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit
Input voltage	High level	V _{IH}		_	2.7~3.6	2.0	_	V
input voitage	Low level	V _{IL}		_	2.7~3.6	_	0.8	V
				I _{OH} = -100 μA	2.7~3.6	V _{CC} - 0.2		
	High level	VoH	V _{IN} = V _{IH} or V _{IL}	$I_{OH} = -6 \text{ mA}$	2.7	2.2		
				$I_{OH} = -8 \text{ mA}$	3.0	2.4		
Output voltage				$I_{OH} = -12 \text{ mA}$	3.0	2.2		V
			$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \mu A$	2.7~3.6	_	0.2	
	Low level	VOI		I _{OL} = 6 mA	2.7	_	0.4	
LOW IS	Low level	VOL		I _{OL} = 8 mA	3.0	_	0.55	
				I _{OL} = 12 mA	3.0	_	0.8	
Input leakage curre	nt	I _{IN}	V _{IN} = 0~3.6 V		2.7~3.6	_	±5.0	μА
2 state output off at	ata aurrant	1	$V_{IN} = V_{IH}$ or V_{IL}		2.7~3.6		100	
3-state output off-state current		loz	V _{OUT} = 0~3.6 V		2.1~3.0	_	±10.0	μА
Power off leakage of	urrent	loff	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μА
Quioscont supply of	Quiescent supply current		V _{IN} = V _{CC} or GND		2.7~3.6	_	20.0	
Quiescent supply co			$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		2.7~3.6	_	±20.0	μΑ
Increase in I _{CC} per	input	Δlcc	$V_{IH} = V_{CC} - 0.6 V$		2.7~3.6	_	750	

DC Characteristics (Ta = $-40~85^{\circ}$ C, 2.3 V \leq V_{CC} \leq 2.7 V)

Characte	ristics	Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit		
Innut voltage	High level	V _{IH}		_	2.3~2.7	1.6	_	V		
Input voltage	Low level	V _{IL}		_	2.3~2.7	_	0.7	V		
				I _{OH} = -100 μA	2.3~2.7	V _{CC} - 0.2	_			
	High level	Voh	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -4 mA	2.3	2.0	_			
					I _{OH} = -6 mA	2.3	1.8	_		
Output voltage				I _{OH} = -8 mA	2.3	1.7	_	V		
				I _{OL} = 100 μA	2.3~2.7	_	0.2			
	Low level	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$V_{IN} = V_{IH}$ or V_{IL}	$V_{IN} = V_{IH}$ or V_{IL}	I _{OL} = 6 mA	2.3	_	0.4	
				I _{OL} = 8 mA	2.3	_	0.6			
Input leakage curre	ent	I _{IN}	V _{IN} = 0~3.6 V		2.3~2.7	_	±5.0	μА		
3-state output off-state current		la-	V _{IN} = V _{IH} or V _{IL}		2.3~2.7	_	±10.0	^		
		loz	V _{OUT} = 0~3.6 V		2.3~2.1	_	±10.0	μА		
Power off leakage	current	loff	V _{IN} , V _{OUT} = 0~3.6 V		0		10.0	μΑ		
Quioscont supply	Out a sent and the sent at		V _{IN} = V _{CC} or GND		2.3~2.7	_	20.0			
Quiescent supply current		Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		2.3~2.7	_	±20.0	μΑ		



DC Characteristics (Ta = -40~85°C, 1.8 V \leq V_{CC} < 2.3 V)

Characteristics		Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit
Input voltage	High level	V _{IH}	_		1.8~2.3	0.7 × V _{CC}	_	V
input voitage	Low level	V _{IL}	-	_	1.8~2.3		0.2 × V _{CC}	V
	High level	VoH	V _{IN} = V _{IH} or V _{IL}	$I_{OH} = -100 \mu A$	1.8	V _{CC} - 0.2		V
Output voltage				$I_{OH} = -4 \text{ mA}$	1.8	1.4		
	Low level	V _{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \mu A$	1.8		0.2	
				I _{OL} = 4 mA	1.8		0.3	
Input leakage currer	Input leakage current		V _{IN} = 0~3.6 V		1.8		±5.0	μΑ
3-state output off-state current		l _{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0 \sim 3.6 \text{ V}$		1.8		±10.0	μА
Power off leakage c	urrent	l _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μΑ
Quiogoant aupply o	0.1		V _{IN} = V _{CC} or GND		1.8	_	20.0	^
Quiescent supply cu	III CIIL	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		1.8		±20.0	μА

AC Characteristics (Ta = -40~85°C, Input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500$ Ω)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Max	Unit
	4		1.8	1.5	9.8	
Propagation delay time	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	0.8	5.6	ns
	t _{pHL}		3.3 ± 0.3	0.6	4.4	
	.		1.8	1.5	9.8	
3-state output enable time	t _{pZL} t _{pZH}	Figure 1, Figure 3	2.5 ± 0.2	0.8	6.6	ns
			3.3 ± 0.3	0.6	5.0	
	t		1.8	1.5	8.5	
3-state output disable time	t _{pLZ}	Figure 1, Figure 3	2.5 ± 0.2	0.8	4.7	ns
	t _{pHZ}		3.3 ± 0.3	0.6	4.2	
	.		1.8	_	0.5	
Output to output skew	tosLH	(Note)	2.5 ± 0.2		0.5	ns
	tosHL		3.3 ± 0.3		0.5	

For $C_L = 50\ pF$, add approximately 300 ps to the AC maximum specification.

Note: This parameter is guaranteed by design.

 $(t_{\text{OSLH}} = |t_{\text{pLHm}} - t_{\text{pLHn}}|, \, t_{\text{OSHL}} = |t_{\text{pHLm}} - t_{\text{pHLn}}|)$

Dynamic Switching Characteristics (Ta = 25°C, Input: $t_r = t_f$ = 2.0 ns, C_L = 30 pF)

Characteristics	Symbol	Test Condition	V _{CC}	(V) Typ.	Unit
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	te) 1.	8 0.15	
Quiet output maximum dynamic V _{OL}	V _{OLP}	V _{IH} = 2.5 V, V _{IL} = 0 V (No	te) 2.	5 0.25	V
		V _{IH} = 3.3 V, V _{IL} = 0 V (No	te) 3.	3 0.35	
	V _{OLV}	$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	te) 1.	8 –0.1	5
Quiet output minimum dynamic V_{OL}		$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	te) 2.	5 –0.2	5 V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	te) 3.	3 –0.3	5
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	te) 1.	8 1.55	
Quiet output minimum dynamic V _{OH}	V _{OHV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	te) 2.	5 2.05	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	te) 3.	3 2.65	

Note: This parameter is guaranteed by design.

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Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition		Тур.	Unit
Characteristics	Symbol	rest condition	V _{CC} (V)	τyp.	
Input capacitance	C _{IN}	DIR, OE	1.8, 2.5, 3.3	6	pF
Bus I/O capacitance	C _{I/O}	An, Bn	1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	$f_{IN} = 10 \text{ MHz}$ (No	e) 1.8, 2.5, 3.3	20	pF

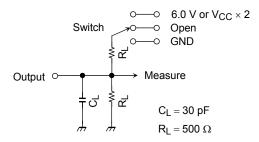
Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

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Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per bit)}$

AC Test Circuit



Parameter	Switch		
t _{pLH} , t _{pHL}		Open	
t _{pLZ} , t _{pZL}	6.0 V V _{CC} × 2	$@V_{CC} = 3.3 \pm 0.3 \text{ V} \\ @V_{CC} = 2.5 \pm 0.2 \text{ V} \\ @V_{CC} = 1.8 \text{ V}$	
t _{pHZ} , t _{pZH}	GND		

Figure 1

AC Waveform

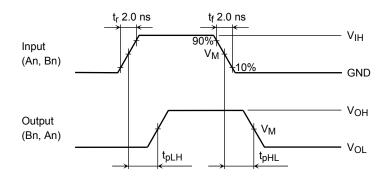


Figure 2 t_{pLH}, t_{pHL}

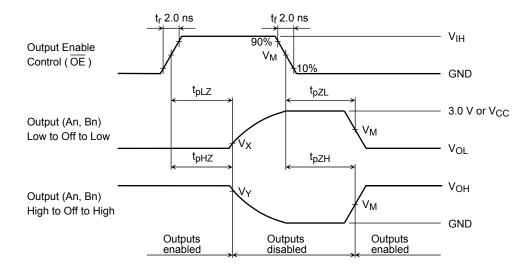


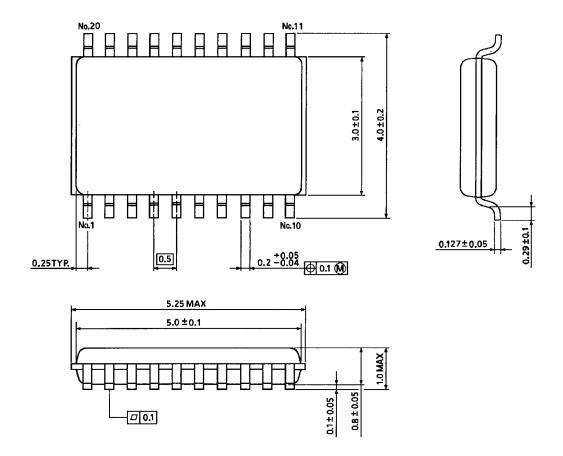
Figure 3 $t_{\text{pLZ}},\,t_{\text{pHZ}},\,t_{\text{pZL}},\,t_{\text{pZH}}$

Cumbal	V _{CC}					
Symbol	$3.3\pm0.3~\textrm{V}$	2.5 ± 0.2 V	1.8 V			
V _{IH}	2.7 V	V _{CC}	V _{CC}			
V _M	1.5 V	V _{CC} /2	V _{CC} /2			
VX	V _{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V			
V_{Y}	V _{OH} – 0.3 V	V _{OH} – 0.15 V	V _{OH} – 0.15 V			

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Package Dimensions



Weight: 0.03 g (typ.)

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20070701-EN GENERAL

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